

2 A low V_F MEGA Schottky barrier rectifier Rev. 01 — 16 October 2009

Product data sheet

Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD128 small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Average forward current: I_{F(AV)} ≤ 2 A
- Reverse voltage: V_R ≤ 30 V
- Low forward voltage
- High power capability due to clip-bond technology
- AEC-Q101 qualified
- Small and flat lead SMD plastic package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

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Quick reference data Table 1. $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Parameter	Conditions	Min	Тур	Max	Unit
average forward current	square wave; $\delta = 0.5$; $f = 20 \text{ kHz}$				
	$T_{amb} \le 100 ^{\circ}C$	<u>[1]</u> _	-	2	Α
	T _{sp} ≤ 140 °C	-	-	2	Α
reverse voltage		-	-	30	V
forward voltage	I _F = 2 A	-	400	450	mV
reverse current	$V_R = 30 \text{ V}$	-	35	100	μΑ
	average forward current reverse voltage forward voltage	$average \ forward \ current \\ & \begin{cases} \delta = 0.5; \\ f = 20 \ kHz \\ \hline T_{amb} \leq 100 \ ^{\circ}C \\ \hline T_{sp} \leq 140 \ ^{\circ}C \end{cases}$ reverse voltage $I_F = 2 \ A$	$\begin{array}{c} \text{average forward current} & \begin{array}{c} \text{square wave;} \\ \delta = 0.5; \\ \text{f} = 20 \text{ kHz} \end{array} \\ \hline T_{amb} \leq 100 ^{\circ}\text{C} \qquad \begin{array}{c} \boxed{11} \ - \\ \hline T_{sp} \leq 140 ^{\circ}\text{C} \qquad - \end{array} \\ \\ \text{reverse voltage} & - \\ \text{forward voltage} & I_F = 2 \text{A} \qquad - \end{array}$	$average \ forward \ current \\ \begin{cases} \delta = 0.5; \\ f = 20 \ kHz \\ \hline T_{amb} \leq 100 \ ^{\circ}\text{C} & \ ^{\boxed{11}} \ ^{-} & - \\ \hline T_{sp} \leq 140 \ ^{\circ}\text{C} & - & - \\ \hline reverse \ voltage & - & - \\ forward \ voltage & I_F = 2 \ A & - & 400 \\ \end{cases}$	$\label{eq:average forward current} \begin{tabular}{llll} & square wave; \\ $\delta=0.5; \\ f=20 \text{ kHz} \\ \hline $T_{amb} \le 100 \text{ °C} & \begin{tabular}{llll} I & - & 2 \\ \hline $T_{sp} \le 140 \text{ °C} & - & - & 2 \\ \hline \hline reverse voltage & - & - & 30 \\ \hline forward voltage & I_F=2 \text{ A} & - & 400 & 450 \\ \hline \end{tabular}$

^[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.



2 A low V_F MEGA Schottky barrier rectifier

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	cathode	[1]	. [4]
2	anode	1 2	1 1 2
		<u> </u>	sym001

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information

Type number	Package	² ackage		
	Name	Description	Version	
PMEG3020BEP	-	plastic surface-mounted package; 2 leads	SOD128	

4. Marking

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Table 4. Marking codes

Type number	Marking code
PMEG3020BEP	A4

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage	T _j = 25 °C	-	30	V
I _{F(AV)}	average forward current	square wave; $\delta = 0.5$; $f = 20 \text{ kHz}$			
		$T_{amb} \le 100 ^{\circ}C$	<u>[1]</u> _	2	Α
		$T_{sp} \le 140 ^{\circ}C$	-	2	Α
I _{FSM}	non-repetitive peak forward current	square wave; $t_p = 8 \text{ ms}$	[2] _	50	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[3][4]	625	mW
			[3][5]	1050	mW
			[3][1]	2100	mW

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2 A low V_F MEGA Schottky barrier rectifier

Limiting values ...continued Table 5.

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
T_j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [2] $T_i = 25$ °C prior to surge.
- Reflow soldering is the only recommended soldering method.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$ thermal resistance f junction to ambient	thermal resistance from	n in free air	[1][2]			
	junction to ambient		[3]	-	200	K/W
			<u>[4]</u> _	-	120	K/W
			<u>[5]</u> _	-	60	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		<u>[6]</u> _	-	12	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Reflow soldering is the only recommended soldering method.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm². [4]
- Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- Soldering point of cathode tab.

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2 A low V_F MEGA Schottky barrier rectifier

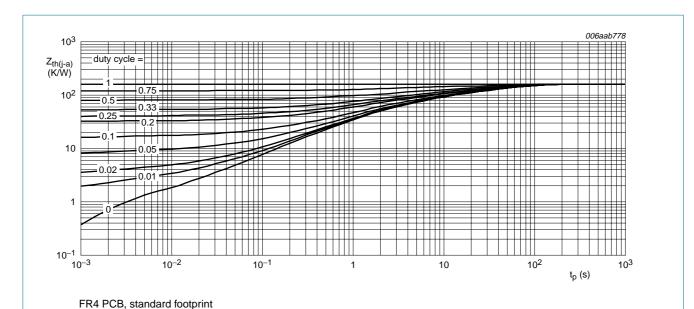


Fig 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

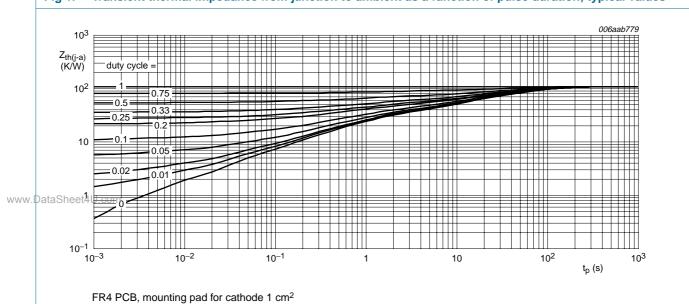
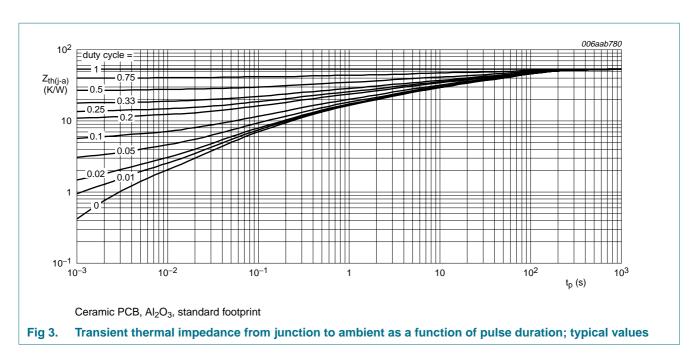


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

2 A low V_F MEGA Schottky barrier rectifier



7. Characteristics

Table 7. Characteristics

 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage	$I_F = 0.1 A$	-	290	340	mV
		I _F = 0.5 A	-	340	400	mV
		I _F = 1 A	-	365	420	mV
		I _F = 1.5 A	-	385	440	mV
		I _F = 2 A	-	400	450	mV
I _R	reverse current	V _R = 5 V	-	4	-	μΑ
		V _R = 10 V	-	6	-	μΑ
		V _R = 30 V	-	35	100	μΑ
C _d diode capacitance	f = 1 MHz					
		V _R = 1 V	-	340	-	pF
		V _R = 10 V	-	120	-	pF

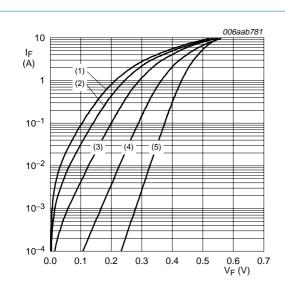
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6 of 13

PMEG3020BEP

2 A low V_F MEGA Schottky barrier rectifier

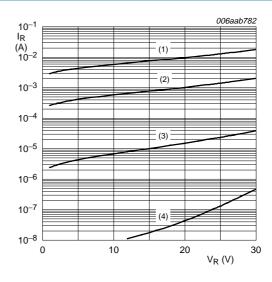


- (1) $T_i = 150 \,^{\circ}\text{C}$
- (2) $T_i = 125 \, ^{\circ}C$
- (3) $T_i = 85 \, ^{\circ}C$
- (4) $T_j = 25 \, ^{\circ}C$
- (5) $T_i = -40 \, ^{\circ}C$

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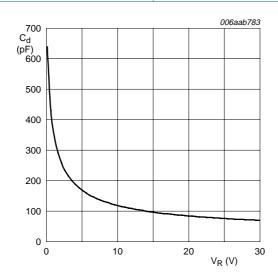
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Fig 4. Forward current as a function of forward voltage; typical values



- (1) $T_i = 125 \,^{\circ}\text{C}$
- (2) $T_j = 85 \,^{\circ}C$
- (3) $T_j = 25 \, ^{\circ}C$
- (4) $T_j = -40 \, ^{\circ}C$

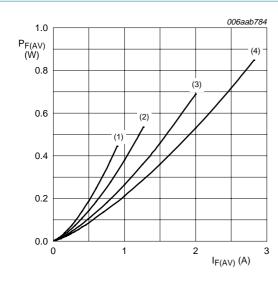
Fig 5. Reverse current as a function of reverse voltage; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$

Fig 6. Diode capacitance as a function of reverse voltage; typical values

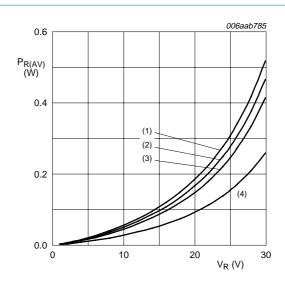
2 A low V_F MEGA Schottky barrier rectifier



T_i = 150 °C

- (1) $\delta = 0.1$
- (2) $\delta = 0.2$
- (3) $\delta = 0.5$
- (4) $\delta = 1$

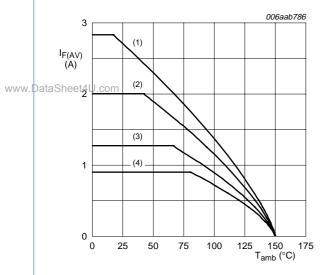
Average forward power dissipation as a Fig 7. function of average forward current; typical values



T_i = 125 °C

- (1) $\delta = 1$
- (2) $\delta = 0.9$
- (3) $\delta = 0.8$
- (4) $\delta = 0.5$

Fig 8. Average reverse power dissipation as a function of reverse voltage; typical values



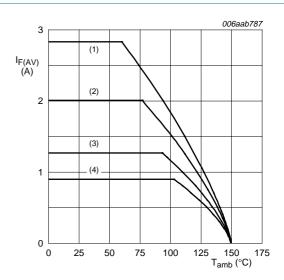
FR4 PCB, standard footprint

(1) $\delta = 1$; DC

Product data sheet

- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

Average forward current as a function of ambient temperature; typical values



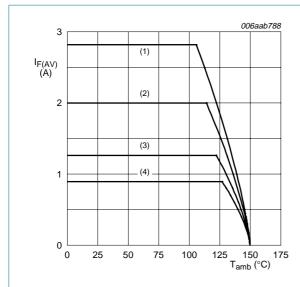
FR4 PCB, mounting pad for cathode 1 cm²

- (1) $\delta = 1$; DC
- (2) $\delta = 0.5$; f = 20 kHz
- (3) $\delta = 0.2$; f = 20 kHz
- (4) $\delta = 0.1$; f = 20 kHz

Fig 10. Average forward current as a function of ambient temperature; typical values

7 of 13

2 A low V_F MEGA Schottky barrier rectifier



Ceramic PCB, Al₂O₃, standard footprint

T_i = 150 °C

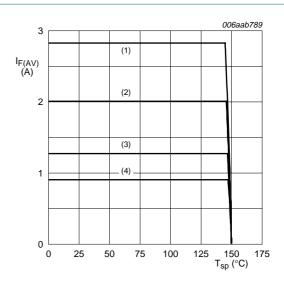
(1) $\delta = 1$; DC

(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig 11. Average forward current as a function of ambient temperature; typical values



T_j = 150 °C

(1) $\delta = 1$; DC

(2) $\delta = 0.5$; f = 20 kHz

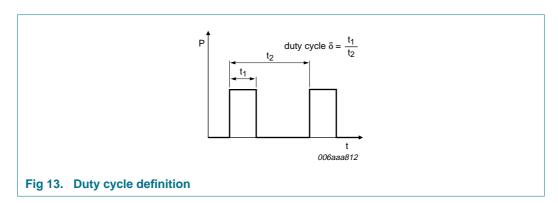
(3) $\delta = 0.2$; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig 12. Average forward current as a function of solder point temperature; typical values

2 A low V_F MEGA Schottky barrier rectifier

8. Test information



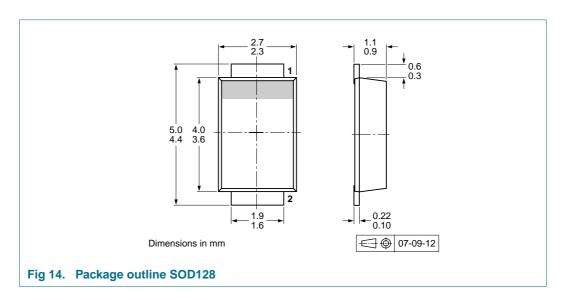
The current ratings for the typical waveforms as shown in <u>Figure 9</u>, <u>10</u>, <u>11</u> and <u>12</u> are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current,

 $I_{RMS}=I_{F(AV)}$ at DC, and $I_{RMS}=I_{M} imes\sqrt{\delta}$ with I_{RMS} defined as RMS current.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



2 A low V_F MEGA Schottky barrier rectifier

10. Packing information

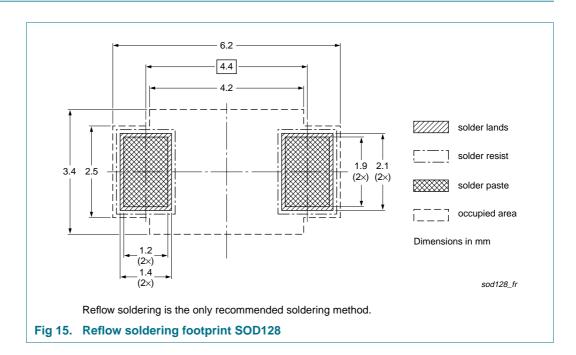
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			3000
PMEG3020BEP	SOD128	4 mm pitch, 12 mm tape and reel	-115

^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering



2 A low V_F MEGA Schottky barrier rectifier

12. Revision history

Table 9. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG3020BEP_1	20091016	Product data sheet	-	-

2 A low V_F MEGA Schottky barrier rectifier

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions"
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2 A low V_F MEGA Schottky barrier rectifier

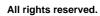
15. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications
1.4	Quick reference data
2	Pinning information
3	Ordering information
4	Marking 2
5	Limiting values
6	Thermal characteristics
7	Characteristics5
8	Test information
8.1	Quality information
9	Package outline 9
10	Packing information
11	Soldering 10
12	Revision history
13	Legal information
13.1	Data sheet status
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks12
14	Contact information
15	Contents

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